

NISTTech

MEMORY CELL INCLUDING ELECTRET AND RANDOM ACCESS MEMORY THEREOF

Docket: 14-019

Abstract

GeRAM is a memory technology that utilize the combined advantage two novel concepts, namely dual-condition programming and polymer electret with high glass-transition temperature (T_g) to achieve the quality of universal memory - non-volatile, fast, high-density, long retention, high endurance, and low cost. It is a realistic candidate for next generation memory.

Status of Availability

This invention is available for licensing exclusively or non-exclusively in any field of use.

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